

Figure 1

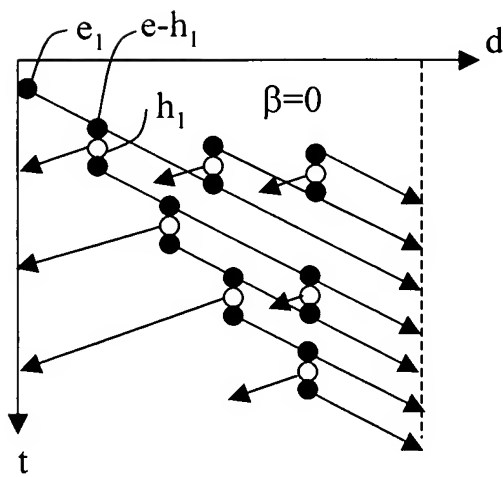


Figure 2a

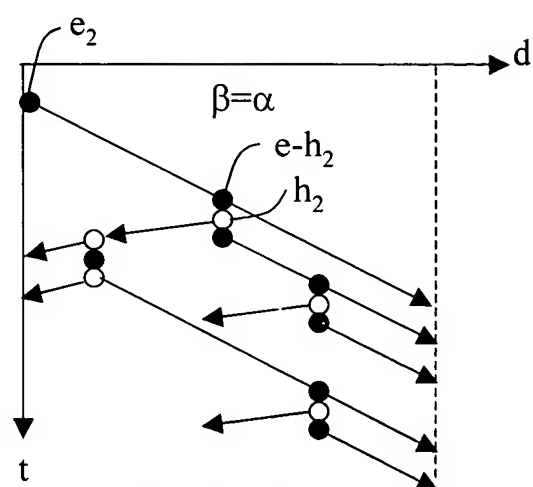


Figure 2b

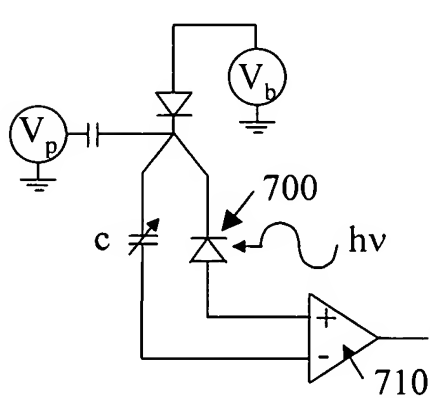


Figure 7a

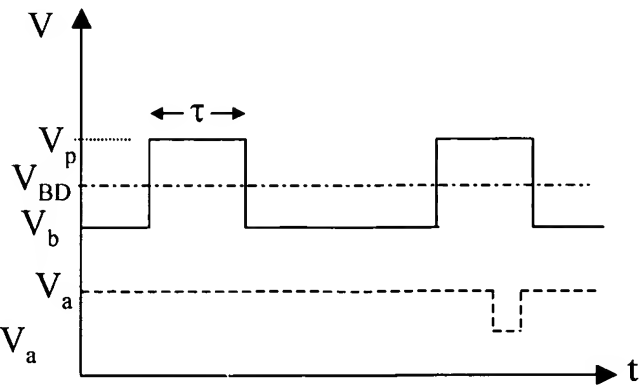


Figure 7b

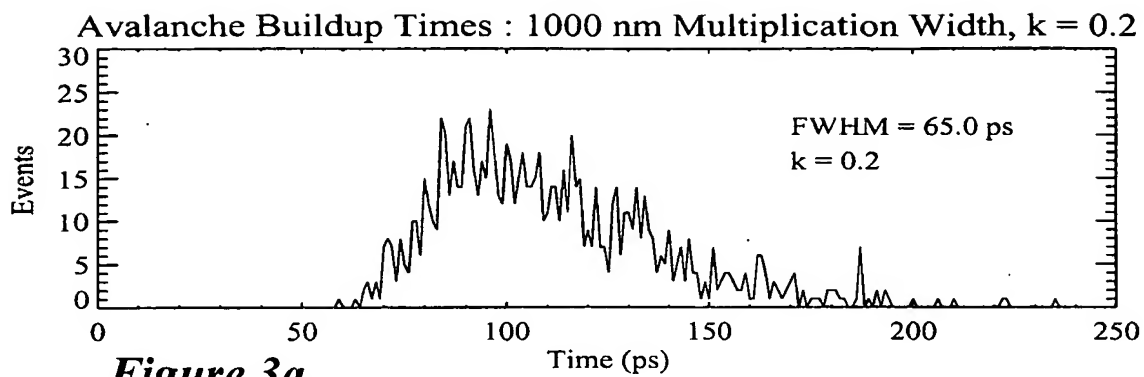


Figure 3a

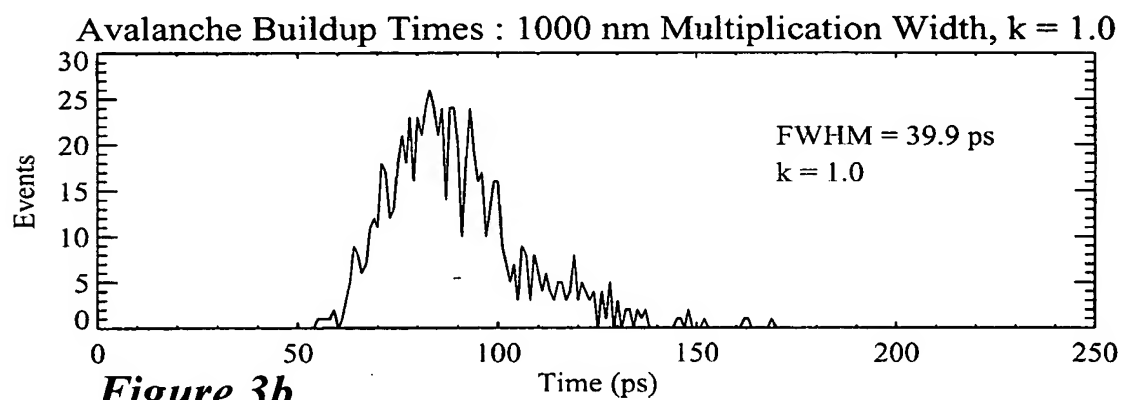
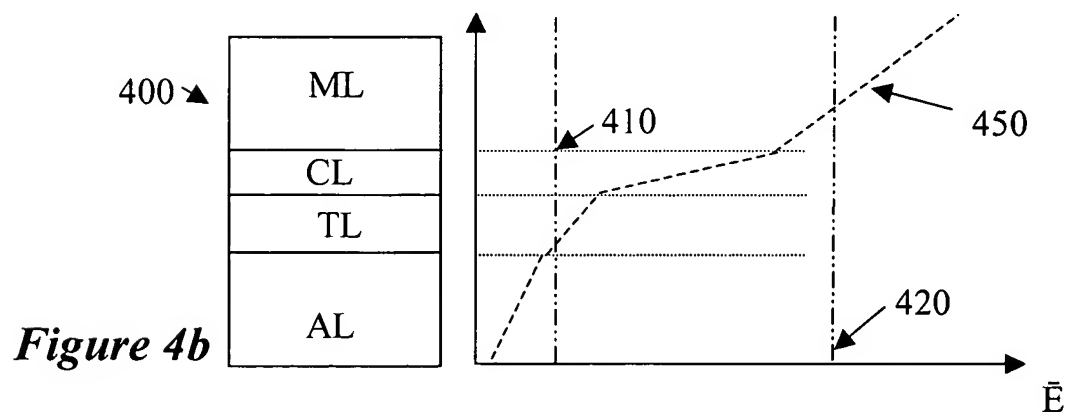
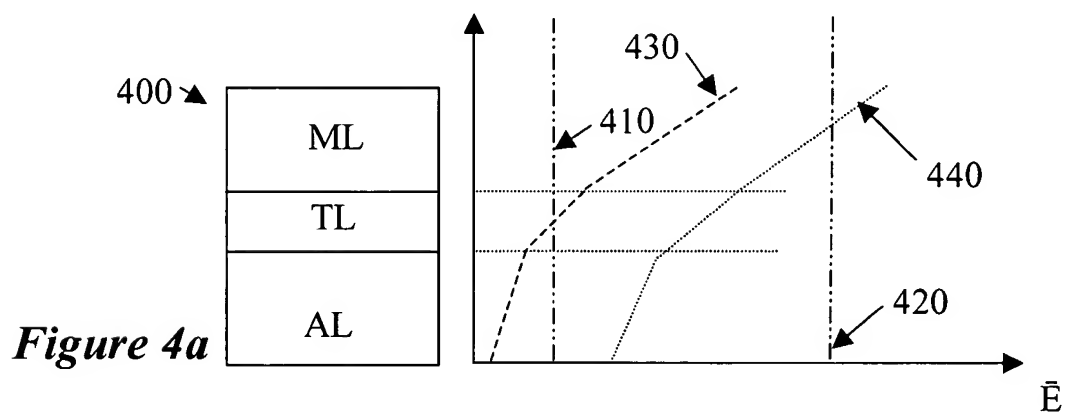


Figure 3b



580 Metallization Contact Layer
570 p^+ -InP Layer
560 i -InP Multiplication Layer
550 n -InP Field Control Layer
540 n -InGaAsP Grading Layer
530 n -InGaAs or n -InGaAsP Absorber
520 i -InGaAs or i -InGaAsP Absorber
510 n^+ -InP Buffer Layer
500 n^+ -InP Substrate

Figure 5

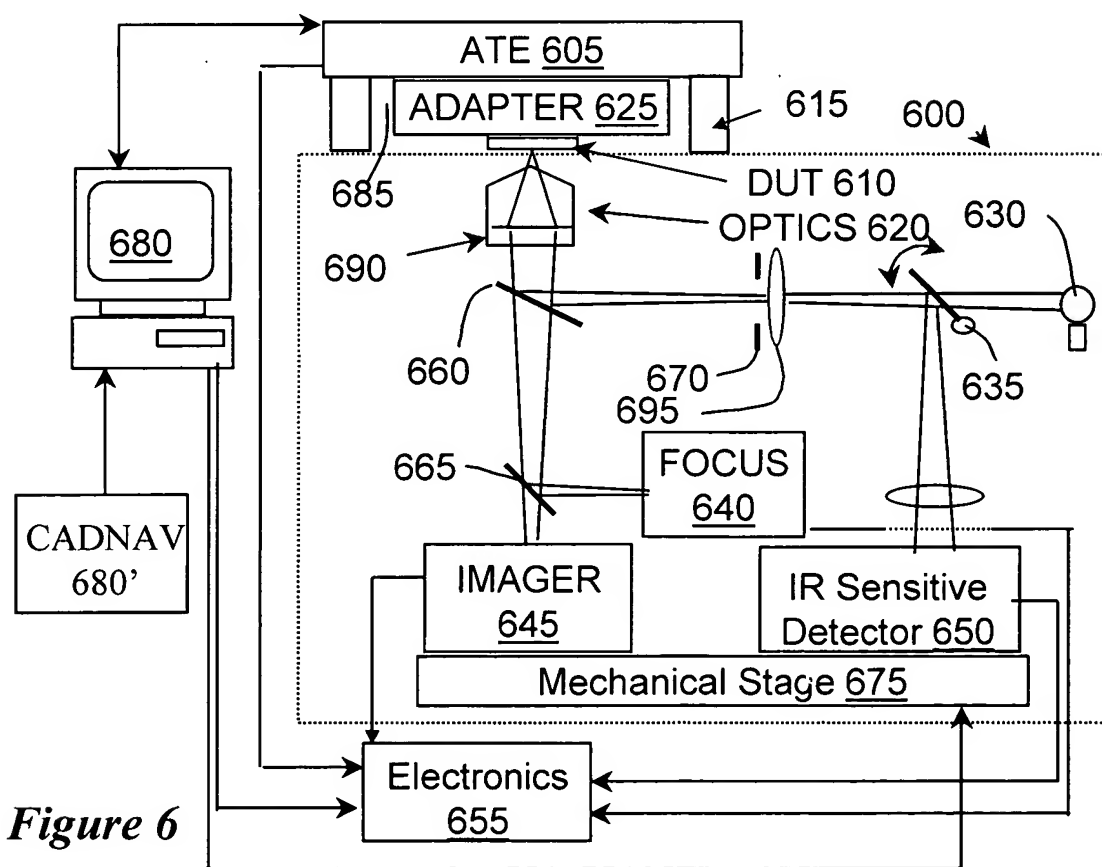


Figure 6